

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	2	"20040181761"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 10:33
L5	9	((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3 or simulat\$3) near3 (characteristic or parameter or electric\$3)) same ((measur\$3 or obtain\$3) near3 (parameter or charactersitic or electric\$3)) same transistor same gate and (simulat\$3 or SPICE)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 11:33
L6	7	((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3 or simulat\$3) near3 (characteristic or parameter or electric\$3)) same ((measur\$3 or obtain\$3) near3 (parameter or charactersitic or electric\$3)) same transistor same gate same (simulat\$3 or SPICE)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 11:48
L7	4	((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3 or simulat\$3) near3 (characteristic or parameter or electric\$3)) same (transistor near3 (arrang\$3 or plac\$3 or rearrang\$3 or dispos\$3 or array or position\$3)) same gate and (simulat\$3 or SPICE)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 11:57
L8	231	((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3 or simulat\$3) near3 (characteristic or parameter or electric\$3)) and (transistor near3 (arrang\$3 or plac\$3 or rearrang\$3 or dispos\$3 or array or position\$3)) same gate and (simulat\$3 or SPICE)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 12:04
L9	16	((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3 or simulat\$3) near3 (characteristic or parameter or electric\$3)) and (transistor near3 (arrang\$3 or plac\$3 or rearrang\$3 or dispos\$3 or array or position\$3)) same gate same (simulat\$3 or SPICE)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 11:58
L10	65	((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3 or simulat\$3) near3 (characteristic or parameter or electric\$3)) and (transistor near3 (arrang\$3 or plac\$3 or rearrang\$3 or dispos\$3 or array or position\$3)) same gate and (simulat\$3 or SPICE) and (first adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 12:06

L11	57	((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3 or simulat\$3) near3 (characteristic or parameter or electric\$3)) and (transistor near3 (arrang\$3 or plac\$3 or rearrang\$3 or dispos\$3 or array or position\$3)) same gate and (simulat\$3 or SPICE) and (first adj transistor) and (second adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 12:08
L12	58	((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3 or simulat\$3) near3 (characteristic or parameter or electric\$3)) and (transistor near3 (arrang\$3 or plac\$3 or rearrang\$3 or dispos\$3 or array or position\$3 or locat\$3 or resid\$3)) same gate and (simulat\$3 or SPICE) and (first adj transistor) and (second adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 12:09
L13	23	((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3) near3 (characteristic or parameter or electric\$3)) and (transistor near3 (arrang\$3 or plac\$3 or rearrang\$3 or dispos\$3 or array or position\$3 or locat\$3 or resid\$3)) same gate and (simulat\$3 or SPICE) and (first adj transistor) and (second adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 12:14
L14	1	((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3) near3 (characteristic or parameter or electric\$3)) and (transistor near3 (arrang\$3 or plac\$3 or rearrang\$3 or dispos\$3 or array or position\$3 or locat\$3 or resid\$3)) same (matrix or array) same gate and (simulat\$3 or SPICE) and (first adj transistor) and (second adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 12:16
L15	0	((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3) near3 (characteristic or parameter or electric\$3)) same (transistor near3 (arrang\$3 or plac\$3 or rearrang\$3 or dispos\$3 or array or position\$3 or locat\$3 or resid\$3)) same gate and (simulat\$3 or SPICE) and (first adj transistor) and (second adj transistor) and (matrix or array)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 12:17

L16	0	((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3) same (characteristic or parameter or electric\$3)) same (transistor near3 (arrang\$3 or plac\$3 or rearrang\$3 or dispos\$3 or array or position\$3 or locat\$3 or resid\$3)) same gate and (simulat\$3 or SPICE) and (first adj transistor) and (second adj transistor) and (matrix or array)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 12:18
L17	1	((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3) same (characteristic or parameter or electric\$3)) same (transistor near3 (arrang\$3 or plac\$3 or rearrang\$3 or dispos\$3 or array or position\$3 or locat\$3 or resid\$3)) same gate and (simulat\$3 or SPICE) and (matrix or array)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 13:06
L19	2	((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3) same (characteristic or parameter or electric\$3)) same (transistor near3 (matrix or array)) same gate and (simulat\$3 or SPICE)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 13:30
L20	5	((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3) same (characteristic or parameter or electric\$3)) same (transistor near3 (matrix or array)) and (simulat\$3 or SPICE) and (gate same (matrix or (two adj dimensional adj pattern))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 13:32
S1	1	simulat\$3 same transistor same (matrix adj pattern)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 08:48
S2	2	simulat\$3 same transistor same (matrix near3 pattern)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 08:49
S3	991648	simulat\$3 same transistor same matrix same (characteristic parameter) amd gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 15:38
S4	31	simulat\$3 same transistor same matrix same (characteristic parameter) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 09:58

S5	1	simulat\$3 same transistor same matrix same (characteristic parameter) same position and (gate same (length width))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 09:19
S6	4	simulat\$3 same transistor same matrix same (characteristic parameter) same (position area region plac\$3) and (gate same (length width))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 09:21
S7	5	simulat\$3 same transistor same matrix same (characteristic parameter) same (position area region plac\$3 arrang\$3 arrangement) and (gate same (length width))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 09:22
S8	12	simulat\$3 same transistor same matrix same (characteristic parameter) and gate and (threshold near3 volt\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:05
S9	2	simulat\$3 same transistor same matrix same (characteristic parameter) and gate and (threshold near3 volt\$4) and ((first adj transistor) same (measur\$3 comput\$3 calculat\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:07
S10	2	simulat\$3 same transistor same matrix same (characteristic parameter) and gate and (threshold near3 volt\$4) and ((first adj transistor) same (measur\$3 comput\$3 calculat\$3)) and (predict\$3 determin\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:08
S11	4	simulat\$3 same transistor same matrix same (characteristic parameter) and gate and (threshold near3 volt\$4) and (first adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:19
S12	3	simulat\$3 same transistor same matrix same (characteristic parameter) and gate same (threshold near3 volt\$4) and ((first and second and third) adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 12:14
S13	2	simulat\$3 same transistor same matrix same (characteristic parameter) and gate same (threshold near3 volt\$4) and ((first near3 transistor) same (measur\$3 determin\$3)) and ((second and third) near3 transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 12:40

S14	1	simulat\$3 same transistor same matrix same (characteristic parameter) and gate same (threshold near3 volt\$4) and ((first near3 transistor near3 model) same (measur\$3 determin\$3)) and ((second and third) near3 transistor near3 model)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 12:44
S15	1	simulat\$3 same transistor same matrix same (characteristic parameter) and gate same volt\$4 and ((first near3 transistor near3 model) same (measur\$3 determin\$3)) and ((second and third) near3 transistor near3 model)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 12:48
S16	2	simulat\$3 same transistor same matrix same (characteristic parameter) and ((first near3 transistor) near3 (measur\$3 determin\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 14:34
S17	3	simulat\$3 same transistor same (matrix array) same (characteristic parameter) and ((first near3 transistor) near3 (measur\$3 determin\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 14:36
S18	10	simulat\$3 same transistor same (matrix array) same (characteristic parameter) and ((first near3 transistor) same (measur\$3 determin\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 14:51
S19	14	simulat\$3 same transistor same (arrang\$3 plac\$3 plan\$4) same (matrix array) same (characteristic parameter)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 14:53
S20	8	simulat\$3 same transistor same (arrang\$3 plac\$3 plan\$4) same (matrix array) same (characteristic parameter) same gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 14:54
S21	4	simulat\$3 same transistor same matrix same (characteristic parameter) and gate and interpolat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 07:56
S22	0	simulat\$3 same transistor same matrix same (characteristic parameter) same predict\$3 same measur\$3 and gate and interpolat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 15:48

S23	0	simulat\$3 same transistor same matrix same (characteristic parameter) same predict\$3 same measur\$3 and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 15:55
S24	1	simulat\$3 same transistor same matrix same (characteristic parameter) same ((predict\$3 or interpolat\$3) near3 measur\$3) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 15:55
S25	1	simulat\$3 same transistor same matrix same (characteristic parameter) and ((predict\$3 or interpolat\$3) near3 measur\$3) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 15:55
S26	13	simulat\$3 same transistor same matrix same (characteristic parameter) and gate and (interpolat\$3 or predict\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 08:03
S27	12	simulat\$3 same transistor same matrix same (characteristic parameter) and gate and ((interpolat\$3 or predict\$3) same (characteristic parameter))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 09:57
S28	2	simulat\$3 same transistor same matrix and gate and ((interpolat\$3 or predict\$3) same (characteristic parameter) same measur\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 10:17
S29	101	(interpolat\$3 or predict\$3) same (characteristic parameter) same measur\$3 same transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 10:18
S30	43	(interpolat\$3 or predict\$3) same (characteristic parameter) same measur\$3 same transistor same gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 10:25
S31	19	(interpolat\$3 or predict\$3) same (characteristic parameter) same measur\$3 same transistor same gate same volt\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 10:18
S32	0	(interpolat\$3 or predict\$3) same (characteristic parameter) same measur\$3 same transistor same gate same matrix	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 10:19

S33	6	(interpolat\$3 or predict\$3) same (characteristic parameter) same measur\$3 same transistor same gate same (matrix or array or pattern)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 10:24
S34	0	(interpolat\$3 or predict\$3) near3 (characteristic parameter) same measur\$3 same transistor same gate same (matrix or array or pattern)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 10:24
S35	8	(interpolat\$3 or predict\$3) near3 (characteristic parameter) same measur\$3 same transistor same gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 10:44
S36	1	"6723665".PN.	USPAT; USOCR	OR	ON	2005/12/07 10:36
S37	1	"5323343".PN.	USPAT; USOCR	OR	ON	2005/12/07 10:40
S38	15	(interpolat\$3 or predict\$3) near3 (characteristic parameter) same measur\$3 same transistor and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 11:05
S39	11	((interpolat\$3 or predict\$3) near3 (characteristic parameter)) same ((measur\$3 or simulat\$3 or obtain\$3) near3 (parameter charactersitic)) same transistor and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 11:06
S40	4	((interpolat\$3 or predict\$3) near3 (characteristic parameter)) same ((measur\$3 or simulat\$3 or obtain\$3) near3 (parameter charactersitic)) same transistor same gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 13:44
S41	11	((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3) near3 (characteristic parameter)) same ((measur\$3 or simulat\$3 or obtain\$3) near3 (parameter charactersitic)) same transistor same gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 14:53
S42	12	((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3 or simulat\$3) near3 (characteristic parameter)) same ((measur\$3 or obtain\$3) near3 (parameter charactersitic)) same transistor same gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 11:30